

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of Claims:

Claims 1-6 are canceled.

7. (currently amended) A method for fabricating a laminated magnetic shield for an MR read head comprising:

providing a substrate;

forming on said substrate a layer of Al_2O_3 of thickness between 0.5 microns and 10.0 microns;

forming on said Al_2O_3 layer a first layer of ferromagnetic material;

forming on said first layer of ferromagnetic material a layer of ruthenium;

forming on said layer of ruthenium a second layer of ferromagnetic material;

forming on said second layer of ferromagnetic material a dielectric layer;

wherein the layer of ruthenium ~~[[if]]~~ is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 8-19 are canceled.

20. (currently amended) A method for fabricating a laminated magnetic shield for an MR read head comprising:

providing a substrate;

forming on said substrate a first layer of ferromagnetic material;

forming on said first layer of ferromagnetic material a first layer of CoFe;

forming on said first layer of CoFe a layer of ruthenium (Ru);

forming on said layer of ruthenium a second layer of CoFe;

forming on said second layer of CoFe a second layer of ferromagnetic material;

forming on said second layer of ferromagnetic material a dielectric layer;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 21-31 are canceled.

32. (currently amended) A laminated magnetic shield for an MR read head comprising:

a substrate;

a layer of Al_2O_3 of thickness between 0.5 microns and 10.0 microns formed on said substrate;

a first layer of ferromagnetic material formed on said layer of Al_2O_3 ;

a layer of ruthenium formed on said first layer of ferromagnetic material;

a second layer of ferromagnetic material formed on said layer of ruthenium;
a dielectric layer formed on said second layer of ferromagnetic material;
wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 33-43 are canceled.

44. (currently amended) A laminated magnetic shield for an MR read head comprising:

a substrate;
a first layer of ferromagnetic material formed on said substrate;
a first layer of CoFe formed on said first layer of ferromagnetic material;
a layer of ruthenium formed on said first layer of CoFe;
a second layer of CoFe formed on said layer of ruthenium;
a second layer of ferromagnetic material formed on said second layer of CoFe;
a dielectric layer formed on said second layer of ferromagnetic material;
wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 45-51 are canceled.

58. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;
a magnetoresistive sensor element formed on said first laminated magnetic shield;
a second laminated magnetic shield formed on said magnetoresistive sensor;
wherein the first laminated magnetic shield comprises:
a substrate;
a layer of Al_2O_3 of thickness between 0.5 microns and 10.0 microns
formed on said substrate;
a first layer of ferromagnetic material formed on said layer of Al_2O_3 ;
a layer of ruthenium formed on said first layer of ferromagnetic material;
a second layer of ferromagnetic material formed on said layer of
ruthenium;
a dielectric layer formed on said second layer of ferromagnetic material;
wherein the layer of ruthenium is of thickness between 2.0 angstroms
and 4.0 angstroms.

Claims 59-69 are canceled.

70. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;
a magnetoresistive sensor element formed on said first laminated magnetic shield;
a second laminated magnetic shield formed on said magnetoresistive sensor
element;

wherein the first laminated magnetic shield comprises:

a substrate;

a first layer of ferromagnetic material formed on said substrate;

a first layer of CoFe formed on said first layer of ferromagnetic material;

a layer of ruthenium formed on said first layer of CoFe;

a second layer of CoFe formed on said layer of ruthenium;

a second layer of ferromagnetic material formed on said second layer of

CoFe;

a dielectric layer formed on said second layer of ferromagnetic material;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 71-82 are canceled..

83. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;

a magnetoresistive sensor element formed on said first laminated magnetic shield;

a second laminated magnetic shield formed on said magnetoresistive sensor element;

wherein the second laminated magnetic shield comprises:

a substrate;

a layer of Al_2O_3 of thickness between 0.5 microns and 10 microns formed on said substrate;

a first layer of ferromagnetic material formed on said layer of Al_2O_3 ;

a layer of ruthenium formed on said first layer of ferromagnetic material;

a second layer of ferromagnetic material formed on said layer of ruthenium;

a dielectric layer formed on said second layer of ferromagnetic material;

wherein the layer of ruthenium [[if]] is of thickness between 2.0 angstroms and 4.0 angstroms.

Claims 84-94 are canceled.

95. (currently amended) A magnetoresistive read head with laminated magnetic shields comprising:

a first laminated magnetic shield;

a magnetoresistive sensor element formed on said first laminated magnetic shield;

a second laminated magnetic shield formed on said magnetoresistive sensor element;

wherein the second laminated magnetic shield comprises:

a substrate;

a first layer of ferromagnetic material formed on said substrate;

a first layer of CoFe formed on said first layer of ferromagnetic material;

a layer of ruthenium formed on said first layer of CoFe;

a second layer of CoFe formed on said layer of ruthenium;

a second layer of ferromagnetic material formed on said second layer of
CoFe;

a dielectric layer formed on said second layer of ferromagnetic material;

wherein the layer of ruthenium is of thickness between 2.0 angstroms
and 4.0 angstroms.